

KSR2210

PNP EPITAXIAL SILICON TRANSISTOR

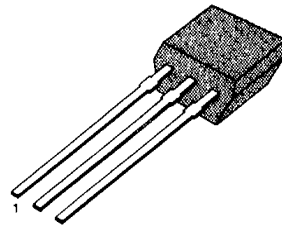
SWITCHING APPLICATION (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor ($R=10k\Omega$)
- Complement to KSR1210

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ 150	$^\circ\text{C}$

TO-92S

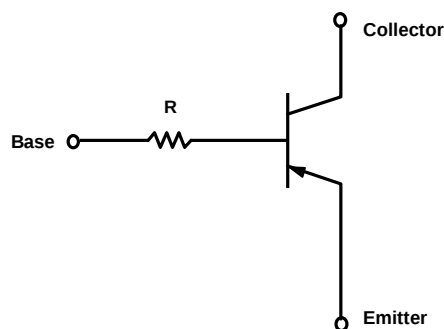


1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -100\mu\text{A}$, $I_E = 0$	-40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_E = -1\text{mA}$, $I_B = 0$	-40			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30\text{V}$, $I_E = 0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -5\text{V}$, $I_C = -1\text{mA}$	100		600	
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$			-0.3	V
Output Capacitance	C_{OB}	$V_{CB} = -10\text{V}$, $I_E = 0$ $f = 1\text{MHz}$		5.5		pF
Current Gain-Bandwidth Product	f_T	$V_{CE} = -10\text{V}$, $I_C = -5\text{mA}$		200		MHz
Input Resistor	R		7	10	13	$k\Omega$

Equivalent Circuit



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